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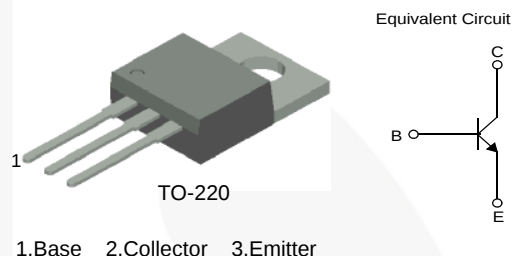
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KSC5502

NPN Planar Silicon Transistor

Features

- High-Voltage Power Switch Mode Application
- Small Variance in Storage Time
- Wide Safe Operating Area
- Suitable for Electronic Ballast Application



Ordering Information

Part Number	Marking	Package	Packing Method
KSC5502TU	J5502	TO-220	Tube

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	1200	V
V_{CEO}	Collector-Emitter Voltage	600	V
V_{EBO}	Emitter-Base Voltage	12	V
I_C	Collector Current (DC)	2	A
I_{CP}	Collector Current (Pulse) ⁽¹⁾	4	A
I_B	Base Current (DC)	1	A
I_{BP}	Base Current (Pulse) ⁽¹⁾	2	A
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Junction Temperature Range	-65 to +150	$^\circ\text{C}$
EAS	Avalanche Energy ($T_J = 25^\circ\text{C}$)	2.5	mJ

Notes:

1. Pulse test: pulse width = 5 ms, duty cycle $\leq 10\%$

Thermal Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Max.	Unit
P_C	Collector Dissipation ($T_C = 25^\circ\text{C}$)	50	W
$R_{\theta JC}^{(2)}$	Thermal Resistance, Junction to Case	2.5	$^\circ\text{C/W}$
$R_{\theta JA}^{(3)}$	Thermal Resistance, Junction to Ambient	85	$^\circ\text{C/W}$

Notes:

- $R_{\theta JC}$ test fixture under infinite cooling condition.
- $R_{\theta JA}$ test board and fixture under natural convection, JE51-10 recommended thermal test board.

Electrical Characteristics⁽⁴⁾

Values are at $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 1\text{ mA}, I_E = 0$	1200	1350		V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 5\text{ mA}, I_B = 0$	600	750		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 500\text{ }\mu\text{A}, I_C = 0$	12.0	13.2		V
I_{CES}	Collector Cut-Off Current	$V_{CES} = 1200\text{ V}, V_{BE} = 0$	$T_C = 25^\circ\text{C}$		100	μA
			$T_C = 125^\circ\text{C}$		500	
I_{CEO}	Collector Cut-Off Current	$V_{CE} = 600\text{ V}, I_B = 0$	$T_C = 25^\circ\text{C}$		100	μA
			$T_C = 125^\circ\text{C}$		500	
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = 12\text{ V}, I_C = 0$	$T_C = 25^\circ\text{C}$		10	μA
h_{FE}	DC Current Gain	$V_{CE} = 1\text{ V}, I_C = 0.2\text{ A}$	$T_C = 25^\circ\text{C}$	15	28	40
			$T_C = 125^\circ\text{C}$	8	27	
		$V_{CE} = 1\text{ V}, I_C = 1\text{ A}$	$T_C = 25^\circ\text{C}$	4.0	8.7	
			$T_C = 125^\circ\text{C}$	3.0	6.6	
		$V_{CE} = 2.5\text{ V}, I_C = 0.5\text{ A}$	$T_C = 25^\circ\text{C}$	12	20	30
			$T_C = 125^\circ\text{C}$	6	16	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 0.2\text{ A}, I_B = 0.02\text{ A}$	$T_C = 25^\circ\text{C}$		0.09	0.80
			$T_C = 125^\circ\text{C}$		0.13	1.10
		$I_C = 0.4\text{ A}, I_B = 0.08\text{ A}$	$T_C = 25^\circ\text{C}$		0.08	0.60
			$T_C = 125^\circ\text{C}$		0.12	1.00
		$I_C = 1\text{ A}, I_B = 0.2\text{ A}$	$T_C = 25^\circ\text{C}$		0.19	1.50
			$T_C = 125^\circ\text{C}$		0.35	3.00
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 0.4\text{ A}, I_B = 0.08\text{ A}$	$T_C = 25^\circ\text{C}$		0.77	1.00
			$T_C = 125^\circ\text{C}$		0.65	0.90
		$I_C = 1\text{ A}, I_B = 0.2\text{ A}$	$T_C = 25^\circ\text{C}$		0.83	1.20
			$T_C = 125^\circ\text{C}$		0.70	1.00
C_{ib}	Input Capacitance	$V_{EB} = 8\text{ V}, I_C = 0, f = 1\text{ MHz}$		410	500	pF
C_{ob}	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$		20	100	pF

Note:

- Pulse test : pulse width = 5 ms, duty cycle $\leq 10\%$

Electrical Characteristics (Continued)Values are at $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions		Min	Typ.	Max.	Unit	
$V_{CE(DSAT)}$	Dynamic Saturation Voltage	$I_C = 0.4\text{ A}, I_{B1} = 80\text{ mA}, V_{CC} = 300\text{ V}$	at $1\mu\text{s}$		11		V	
			at $3\mu\text{s}$		8			
		$I_C = 1\text{ A}, I_{B1} = 200\text{ mA}, V_{CC} = 300\text{ V}$	at $1\mu\text{s}$		23			
			at $3\mu\text{s}$		13			
Resistive Load Switching (D.C $\leq$ 10%, Pulse Width = 20 s)								
t_{ON}	Turn-On Time	$I_C = 0.4\text{ A}, I_{B1} = 80\text{ mA}, I_{B2} = 0.2\text{ A}, V_{CC} = 300\text{ V}, R_L = 750\ \Omega$	$T_C = 25^\circ\text{C}$		250	350	ns	
			$T_C = 125^\circ\text{C}$		260			
t_{OFF}	Turn-Off Time		$T_C = 25^\circ\text{C}$		3.3	4.0	μs	
			$T_C = 125^\circ\text{C}$		3.8			
t_{ON}	Turn-On Time	$I_C = 1\text{ A}, I_{B1} = 160\text{ mA}, I_{B2} = 160\text{ mA}, V_{CC} = 300\text{ V}, R_L = 300\ \Omega$	$T_C = 25^\circ\text{C}$		220	450	ns	
			$T_C = 125^\circ\text{C}$		250			
t_{OFF}	Turn-Off Time		$T_C = 25^\circ\text{C}$		4.3	5.0	μs	
			$T_C = 125^\circ\text{C}$		5.0			
Inductive Load Switching ($V_{CC} = 15\text{ V}$)								
t_{STG}	Storage Time	$I_C = 0.4\text{ A}, I_{B1} = 80\text{ mA}, I_{B2} = 0.2\text{ A}, V_Z = 300\text{ V}, L_C = 200\ \mu\text{H}$	$T_C = 25^\circ\text{C}$		1.4	2.0	μs	
			$T_C = 125^\circ\text{C}$		1.7			
t_F	Fall Time		$T_C = 25^\circ\text{C}$		130	200	ns	
			$T_C = 125^\circ\text{C}$		80			
t_C	Cross-Over Time	$I_C = 0.4\text{ A}, I_{B1} = 80\text{ mA}, I_{B2} = 0.2\text{ A}, V_Z = 300\text{ V}, L_C = 200\ \mu\text{H}$	$T_C = 25^\circ\text{C}$		210	350	ns	
			$T_C = 125^\circ\text{C}$		130			
t_{STG}	Storage Time		$I_C = 0.8\text{ A}, I_{B1} = 160\text{ mA}, I_{B2} = 160\text{ mA}, V_{CC} = 300\text{ V}, L_C = 200\ \mu\text{H}$	$T_C = 25^\circ\text{C}$		4.9	5.5	μs
				$T_C = 125^\circ\text{C}$		5.3		
t_F	Fall Time	$T_C = 25^\circ\text{C}$			170	250	ns	
		$T_C = 125^\circ\text{C}$			340			
t_C	Cross-Over Time	$I_C = 0.8\text{ A}, I_{B1} = 160\text{ mA}, I_{B2} = 160\text{ mA}, V_{CC} = 300\text{ V}, L_C = 200\ \mu\text{H}$	$T_C = 25^\circ\text{C}$		300	600	ns	
			$T_C = 125^\circ\text{C}$		810			

Typical Performance Characteristics

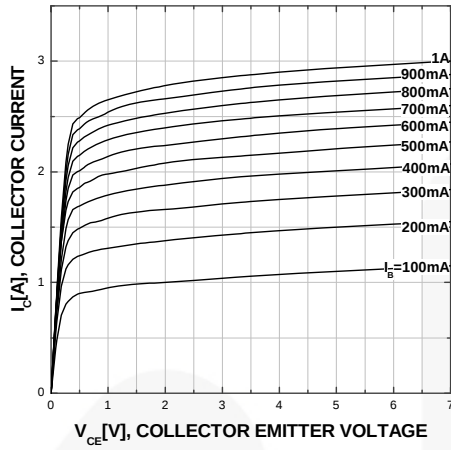


Figure 1. Static Characteristic

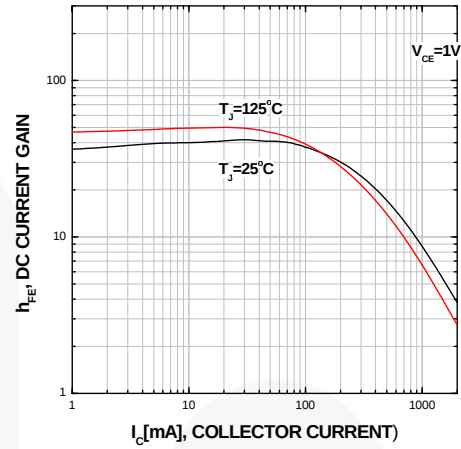


Figure 2. DC current Gain

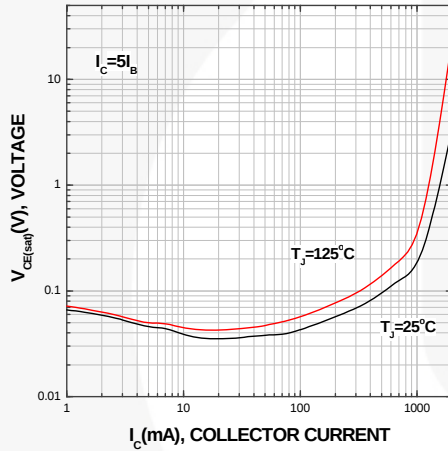


Figure 3. Collector-Emitter Saturation Voltage

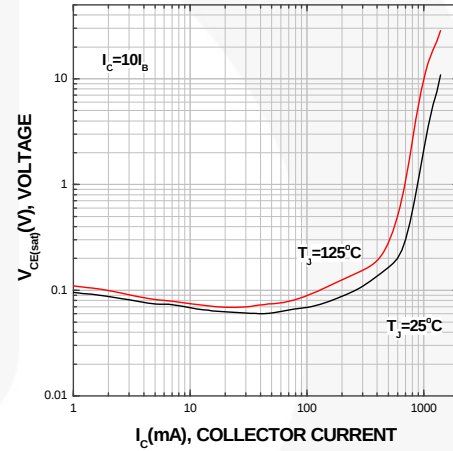


Figure 4. Collector-Emitter Saturation Voltage

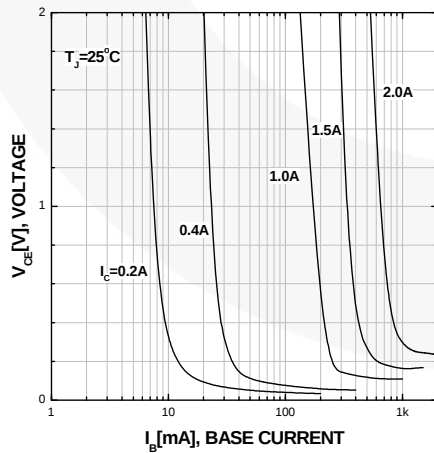


Figure 5. Typical Collector Saturation Voltage

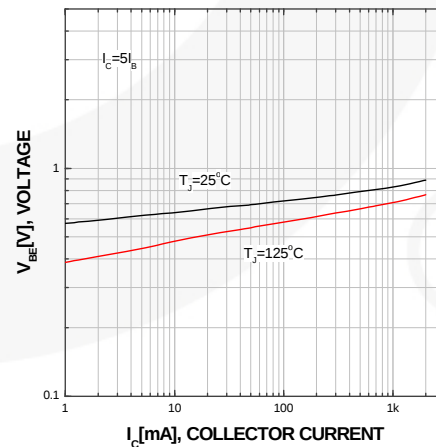


Figure 6. Base-Emitter Saturation Voltage

Typical Performance Characteristics (Continued)

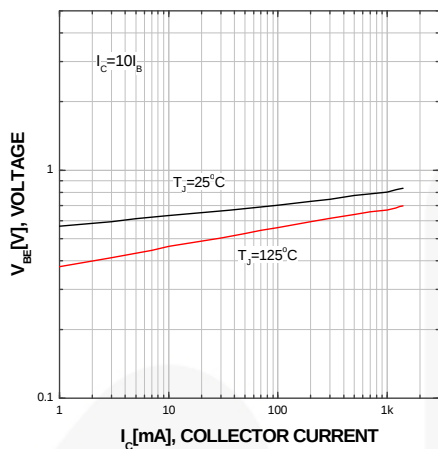
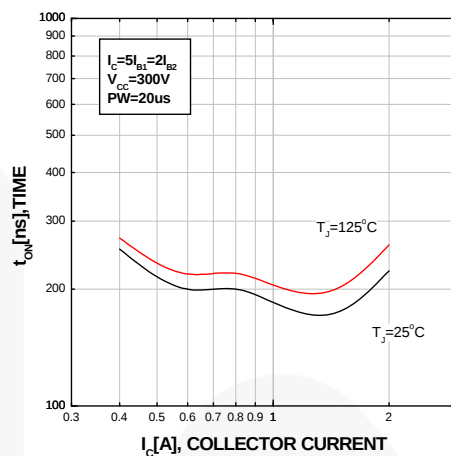
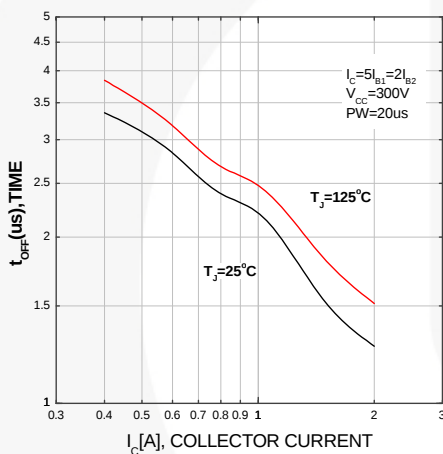
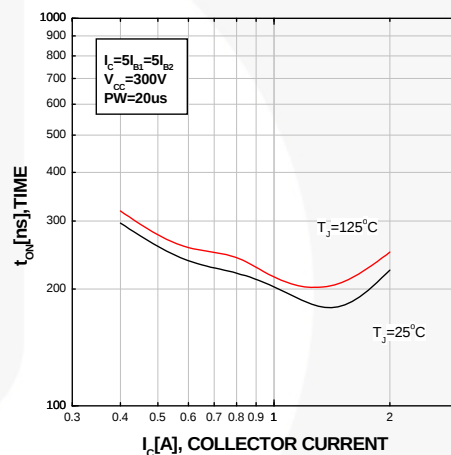
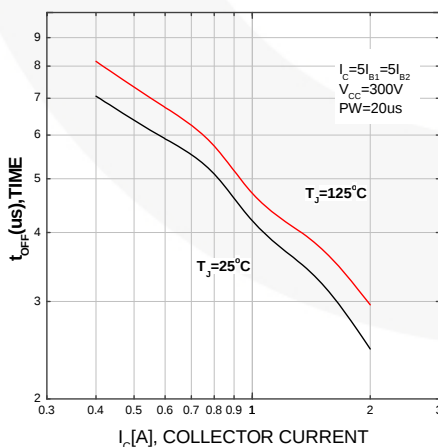
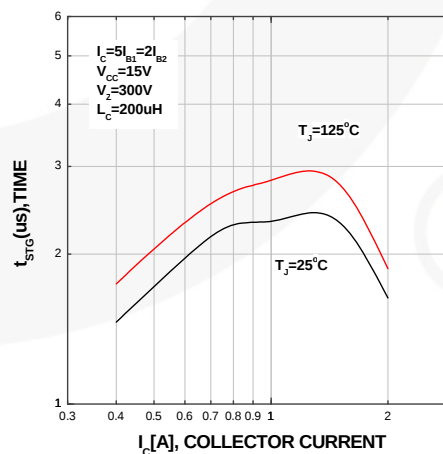


Figure 7. Base-Emitter Saturation Voltage

Figure 8. Resistive Switching Time, t_{on} Figure 9. Resistive Switching Time, t_{off} Figure 10. Resistive Switching Time, t_{on} Figure 11. Resistive Switching Time, t_{off} Figure 12. Inductive Switching Time, t_{STG}

Typical Performance Characteristics (Continued)

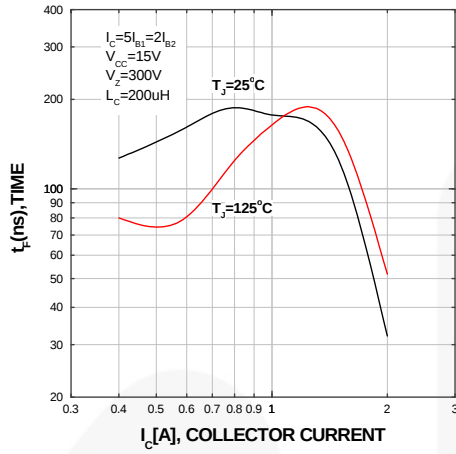


Figure 13. Inductive Switching Time, t_f

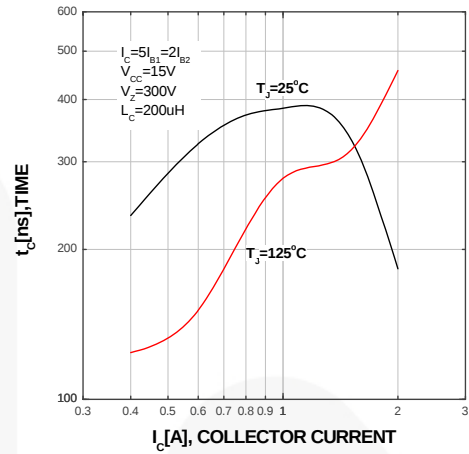


Figure 14. Inductive Switching Time, t_c

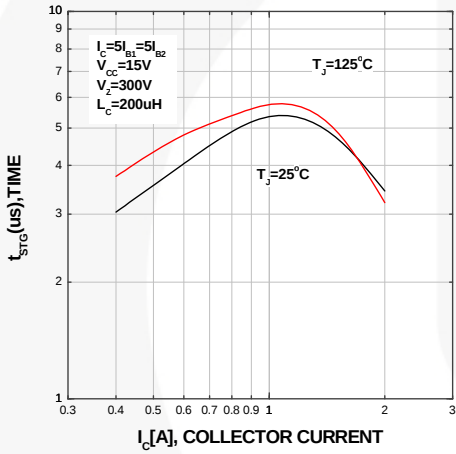


Figure 15. Inductive Switching Time, t_{STG}

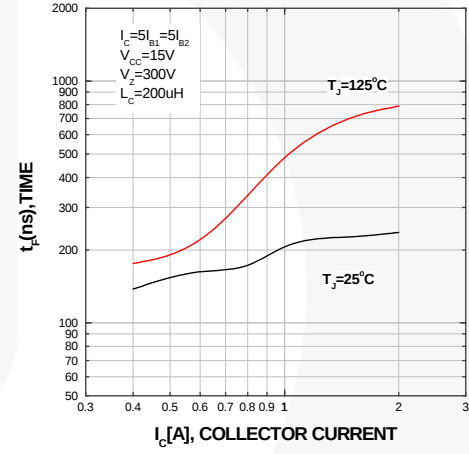


Figure 16. Inductive Switching Time, t_f

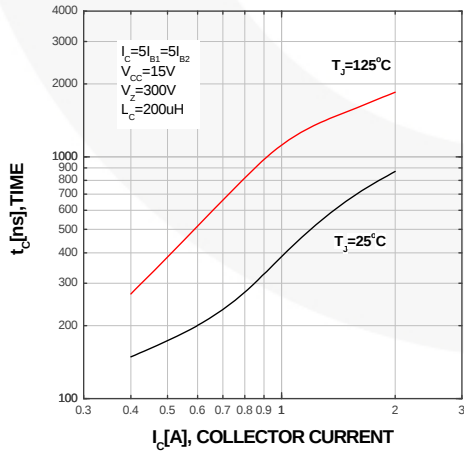


Figure 17. Inductive Switching Time, t_c

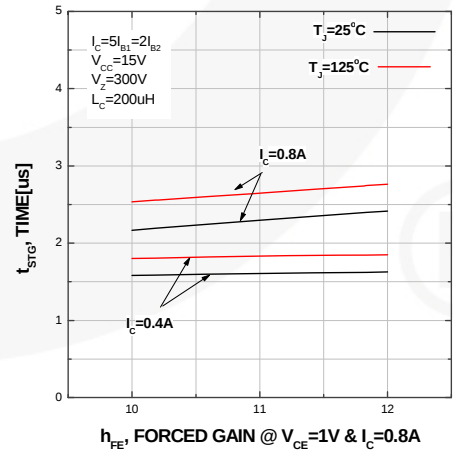


Figure 18. Inductive Switching Time, t_{STG}

Typical Performance Characteristics (Continued)

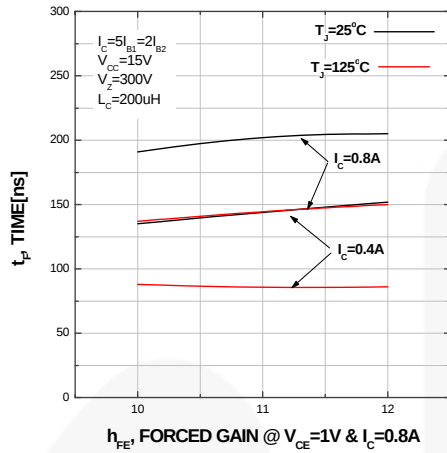


Figure 19. Inductive Switching Time, t_F

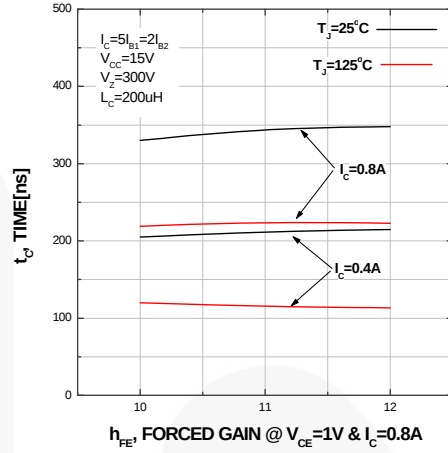


Figure 20. Inductive Switching Time, t_C

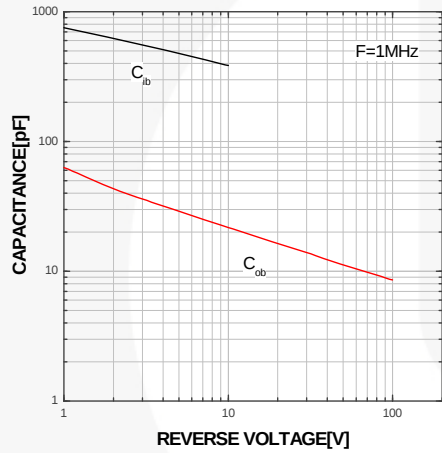


Figure 21. Capacitance

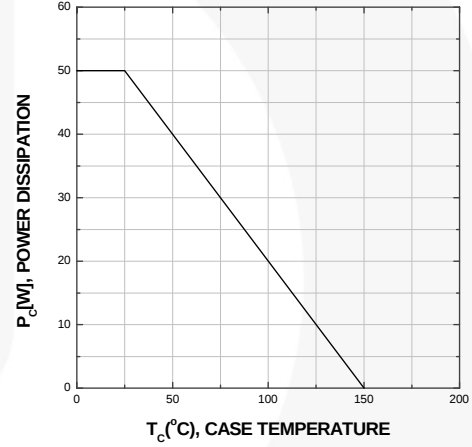


Figure 22. Power Derating

Physical Dimensions

TO-220

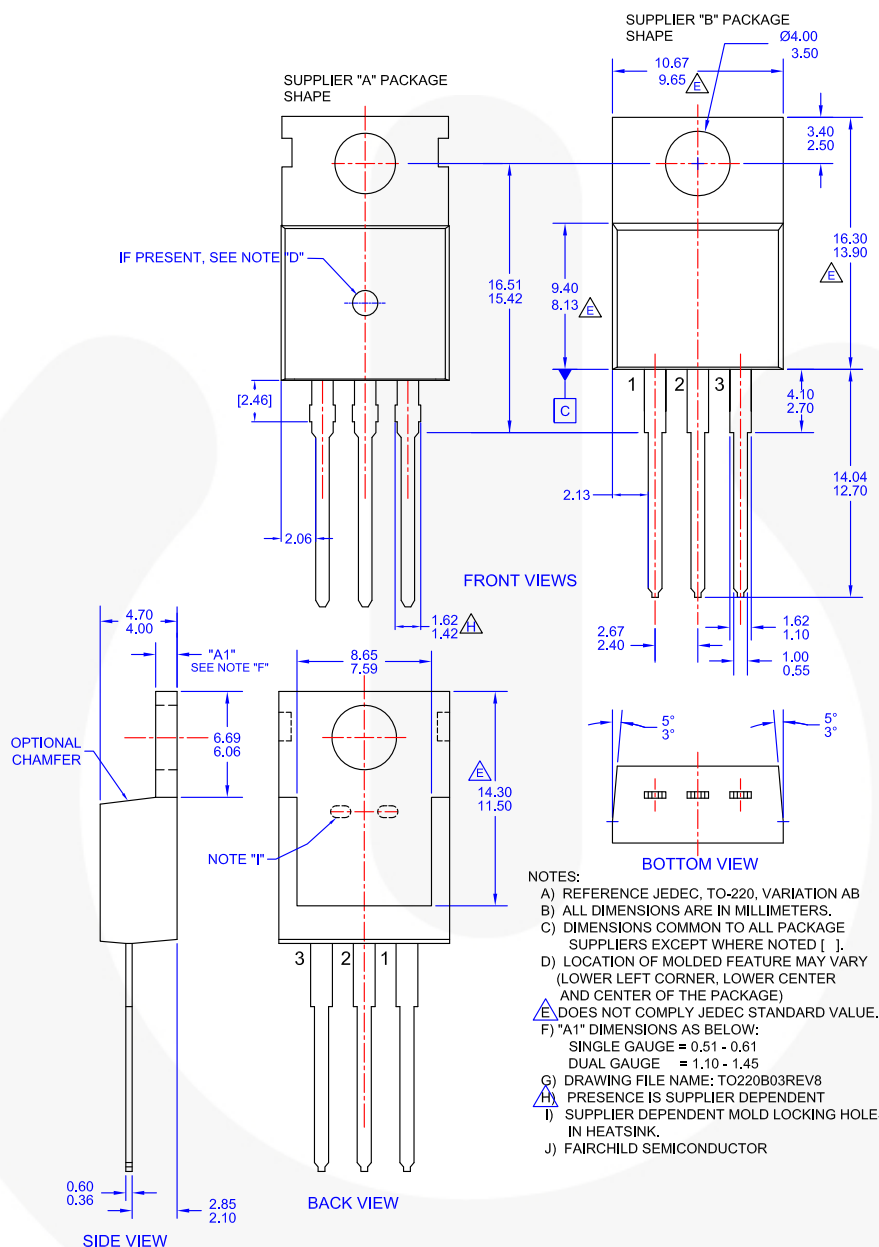


Figure 23. TO-220, MOLDED, 3-LEAD, JEDEC VARIATION AB (ACTIVE)

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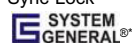
<http://www.fairchildsemi.com/dwg/TO/TO220B03.pdf>.

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FETBench™	OPTOPLANAR®	SupreMOS®	XS™
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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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